Q.P. Code :08593

[Time: 03 Hours] [ Marks: 80 ]

Please check whether you have got the right question paper.

N.B: 1. Q1. Is compulsory.

b) Surface micromachining

d) Si as a MEMS material

c) TCE of a material and its issues.

- 2. Attempt any three out of remaining.
- 3. Assume any suitable data required but justify the same.

Q.1 a)	What is the need of Lift off method? Explain this method with proper diagrams.	20
b)	What is the stiffness constant of microcantilever beam for following given dimensions and a point contact load applied at its tip. E=170GPa, h(thickness) = $10\mu m$ , w(width)= $2\mu m$ & L(Length) = $50\mu m$	
c)	Explain wafer bonding and its techniques.	
d)	Explain scaling of MEMs devices.	
Q.2 a)	Explain any one MEMS device used in modern automobile systems with working principle and representative fabrication process steps.	10
b)	Justify the need of PECVD with its proper schematic and explanation.	10
Q.3 a)	Explain fabrication of any one of the MEMS devices using Bulk micromachining technique.	10
b)	Explain the importance of etch stop techniques with proper illustration.	10
Q.4 a)	Explain the fabrication process steps for microheater. State its advantages over conventional macro sized heater.	10
b)	Name any two polymer materials for MEMS device fabrication. Also explain the importance of these polymer materials for MEMS device fabrication with suitable examples.	10
Q.5 a)	Describe the representative process flow for fabricating the Digital Micro mirror Device (DMD) by Texas Instruments. Also explain its working principle.	10
b)	Define the term TCR. Also describe the method of characterization of TCR.	10
Q.6	Write Short notes on a) DRIE & its significance for MEMS device fabrication.	20

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